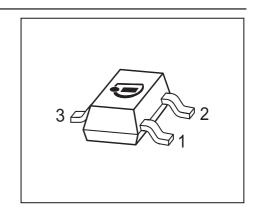


#### **NPN Silicon RF Transistor**

- For modulators and amplifiers in TV and VCR tuners
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101







ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BF771	RBs	1 = B	2 = E	3 = C	SOT23

**Maximum Ratings** 

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	$V_{\sf CEO}$	12	V	
Collector-emitter voltage	V <sub>CES</sub>	20		
Collector-base voltage	$V_{\mathrm{CBO}}$	20		
Emitter-base voltage	$V_{EBO}$	2		
Collector current	/ <sub>C</sub>	80	mA	
Base current	/ <sub>B</sub>	10		
Total power dissipation <sup>2)</sup>	P <sub>tot</sub>	580	mW	
<i>T</i> <sub>S</sub> ≤ 69°C				
Junction temperature	T <sub>i</sub>	150	°C	
Ambient temperature	$T_{A}$	-65 150		
Storage temperature	$T_{ m stg}$	-65 150		

#### **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>3)</sup>	$R_{thJS}$	≤ 140	K/W

1

<sup>&</sup>lt;sup>1</sup>Pb-containing package may be available upon special request

 $<sup>^2</sup>T_{\mbox{\scriptsize S}}$  is measured on the collector lead at the soldering point to the pcb

 $<sup>^3</sup>$ For calculation of  $R_{\mathrm{thJA}}$  please refer to Application Note Thermal Resistance



**Electrical Characteristics** at  $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics				•	•
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	12	-	-	V
$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	, ,				
Collector-emitter cutoff current	I <sub>CES</sub>	-	-	100	μA
$V_{CE} = 20 \text{ V}, \ V_{BE} = 0$					
Collector-base cutoff current	I <sub>CBO</sub>	-	-	100	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	l <sub>EBO</sub>	-	-	1	μA
$V_{EB} = 1 \text{ V}, I_{C} = 0$					
DC current gain-	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, pulse measured					



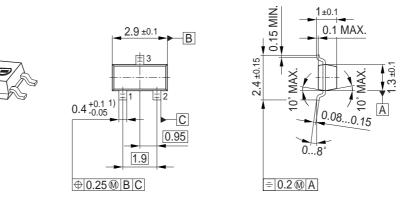
**Electrical Characteristics** at  $T_A = 25$ °C, unless otherwise specified

Parameter Param	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random same	oling)	T			ı
Transition frequency	$f_{T}$	6	8	-	GHz
$I_{\rm C} = 50 \text{ mA}, \ V_{\rm CE} = 8 \text{ V}, \ f = 500 \text{ MHz}$					
Collector-base capacitance	$C_{cb}$	-	0.66	1	pF
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,					
emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	-	0.28	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0,$					
base grounded					
Emitter-base capacitance	$C_{eb}$	-	2.25	-	
$V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{CB} = 0$ ,					
collector grounded					
Noise figure	F				dB
$I_{\rm C} = 10 \text{ mA}, \ V_{\rm CE} = 8 \text{ V}, \ Z_{\rm S} = Z_{\rm Sopt},$					
f = 900 MHz		-	1	-	
$I_{\rm C} = 10 \text{ mA}, \ V_{\rm CE} = 8 \text{ V}, \ Z_{\rm S} = Z_{\rm Sopt} \ ,$					
f = 1.8 GHz		-	1.6	-	
Power gain, maximum available <sup>1)</sup>	G <sub>ma</sub>				
$I_{C} = 30 \text{ mA}, V_{CE} = 8 \text{ V}, Z_{S} = Z_{Sopt}$ ,					
$Z_{L} = Z_{Lopt}$ , $f = 900 \text{ MHz}$		-	15	-	
$I_{C} = 30 \text{ mA}, V_{CE} = 8 \text{ V}, Z_{S} = Z_{Sopt}$ ,					
$Z_{L} = Z_{Lopt}$ , $f = 1.8 \text{ GHz}$		-	10	-	
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB
$I_{\rm C} = 30 \text{ mA}, \ V_{\rm CE} = 8 \text{ V}, \ Z_{\rm S} = Z_{\rm L} = 50 \Omega$ ,					
f = 900 MHz		-	13	-	
$I_{\rm C} = 30 \text{ mA}, \ V_{\rm CE} = 8 \text{ V}, \ Z_{\rm S} = Z_{\rm L} = 50 \Omega \ ,$					
f = 1.8 GHz		-	7.5	-	

 $<sup>{}^{1}</sup>G_{\text{ma}} = |S_{21} / S_{12}| (k-(k^{2}-1)^{1/2})$ 

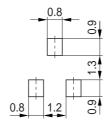


## Package Outline

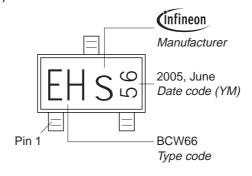


1) Lead width can be 0.6 max. in dambar area

#### Foot Print

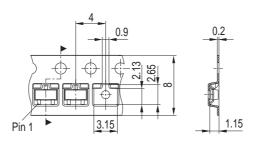


## Marking Layout (Example)



## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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